Document Number: MMG3015NT1

Rev. 3, 9/2012

# **√**RoHS

# Heterojunction Bipolar Transistor Technology (InGaP HBT)

**Broadband High Linearity Amplifier** 

The MMG3015NT1 is a general purpose amplifier that is internally input and output matched. It is designed for a broad range of Class A, small-signal, high linearity, general purpose applications. It is suitable for applications with frequencies from 0 to 6000 MHz such as cellular, PCS, BWA, WLL, PHS, CATV, VHF, UHF, UMTS and general small-signal RF.

#### **Features**

- Frequency: 0-6000 MHzP1dB: 20.5 dBm @ 900 MHz
- Small Signal Gain: 15.5 dB @ 900 MHz
- Third Order Output Intercept Point: 36 dBm @ 900 MHz
- Single 5 Volt Supply
- Active Bias Control
- · Internally Matched to 50 Ohms
- Cost-effective SOT-89 Surface Mount Package
- In Tape and Reel. T1 Suffix = 1,000 Units, 12 mm Tape Width, 7 inch Reel.

# MMG3015NT1

0-6000 MHz, 15.5 dB 20.5 dBm InGaP HBT



CASE 2142-01 SOT-89 PLASTIC

Table 1. Typical Performance (1)

Characteristic	Symbol	900 MHz	2140 MHz	3500 MHz	Unit
Small-Signal Gain (S21)	G <sub>p</sub>	15.5	14.5	12.5	dB
Input Return Loss (S11)	IRL	-15	-19	-19	dB
Output Return Loss (S22)	ORL	-13	-9	-7	dB
Power Output @1dB Compression	P1dB	20.5	20.5	18.5	dBm
Third Order Output Intercept Point	OIP3	36	33.5	30.5	dBm

<sup>1.</sup>  $V_{CC} = 5 \text{ Vdc}$ ,  $T_A = 25^{\circ}\text{C}$ , 50 ohm system.

**Table 2. Maximum Ratings** 

Rating	Symbol	Value	Unit
Supply Voltage	V <sub>CC</sub>	7	V
Supply Current	I <sub>CC</sub>	300	mA
RF Input Power	Pin	12	dBm
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C
Junction Temperature (2)	TJ	150	°C

For reliable operation, the junction temperature should not exceed 150°C.

#### **Table 3. Thermal Characteristics**

Characteristic	Symbol	Value <sup>(3)</sup>	Unit
Thermal Resistance, Junction to Case Case Temperature 95°C, 5 Vdc, 95 mA, no RF applied	$R_{ heta JC}$	41.5	°C/W

3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <a href="http://www.freescale.com/rf">http://www.freescale.com/rf</a>. Select Documentation/Application Notes - AN1955.



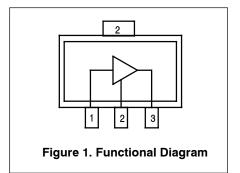
 $\textbf{Table 4. Electrical Characteristics} \ (V_{CC} = 5 \ \text{Vdc}, \ 900 \ \text{MHz}, \ T_{A} = 25^{\circ}\text{C}, \ 50 \ \text{ohm system, in Freescale Application Circuit})$ 

Characteristic	Symbol	Min	Тур	Max	Unit
Small-Signal Gain (S21)	G <sub>p</sub>	14	15.5	_	dB
Input Return Loss (S11)	IRL	_	-15	_	dB
Output Return Loss (S22)	ORL	_	-13	_	dB
Power Output @ 1dB Compression	P1dB	_	20.5	_	dBm
Third Order Output Intercept Point	OIP3	_	36	_	dBm
Noise Figure	NF	_	5.6	_	dB
Supply Current (1)	I <sub>CC</sub>	80	95	120	mA
Supply Voltage (1)	V <sub>CC</sub>		5	_	V

<sup>1.</sup> For reliable operation, the junction temperature should not exceed 150  $^{\circ}\text{C}.$ 

**Table 5. Functional Pin Description** 

	•
Pin Number	Pin Function
1	RF <sub>in</sub>
2	Ground
3	RF <sub>out</sub> /DC Supply



**Table 6. ESD Protection Characteristics** 

Test Methodology	Class
Human Body Model (per JESD 22-A114)	1C
Machine Model (per EIA/JESD 22-A115)	A
Charge Device Model (per JESD 22-C101)	IV

**Table 7. Moisture Sensitivity Level** 

Test Methodology	Rating	Package Peak Temperature	Unit
Per JESD 22-A113, IPC/JEDEC J-STD-020	1	260	°C

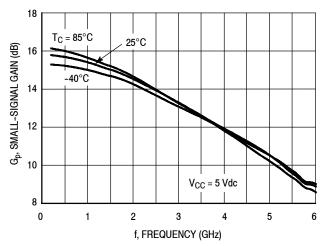


Figure 2. Small-Signal Gain (S21) versus Frequency

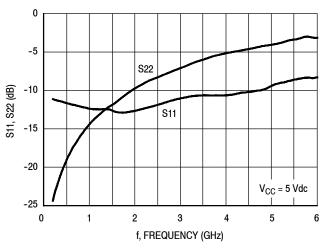


Figure 3. Input/Output Loss versus Frequency

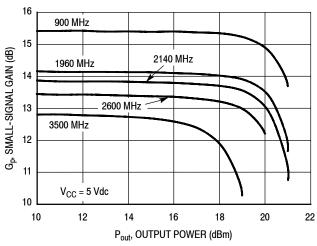


Figure 4. Small-Signal Gain versus Output Power

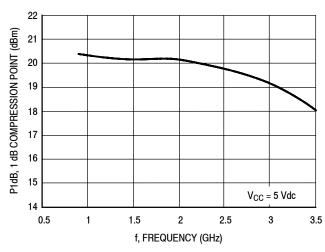


Figure 5. P1dB versus Frequency

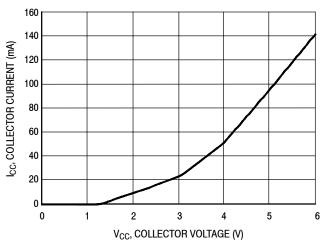


Figure 6. Collector Current versus Collector Voltage

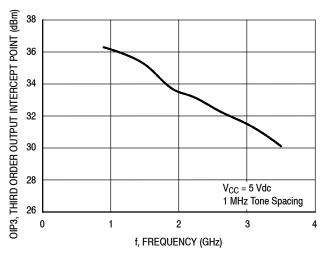


Figure 7. Third Order Output Intercept Point versus Frequency

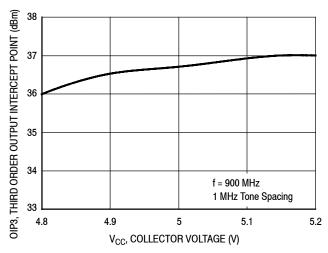


Figure 8. Third Order Output Intercept Point versus Collector Voltage

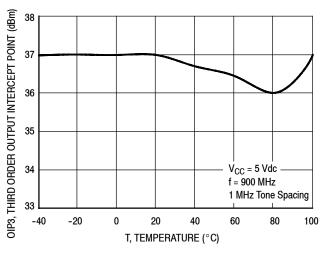


Figure 9. Third Order Output Intercept Point versus Case Temperature

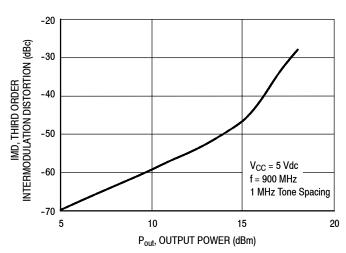
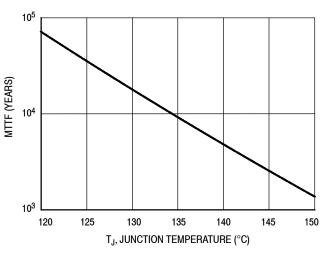


Figure 10. Third Order Intermodulation Distortion versus Output Power



NOTE: The MTTF is calculated with  $V_{CC}$  = 5 Vdc,  $I_{CC}$  = 95 mA

Figure 11. MTTF versus Junction Temperature

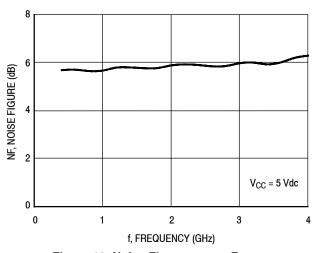


Figure 12. Noise Figure versus Frequency

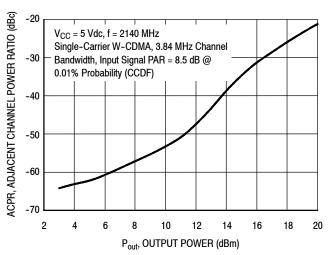


Figure 13. Single-Carrier W-CDMA Adjacent Channel Power Ratio versus Output Power

MMG3015NT1

# 50 OHM APPLICATION CIRCUIT: 40-800 MHz

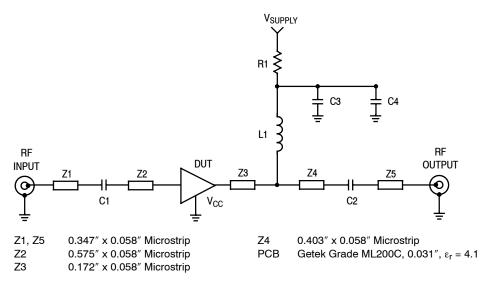
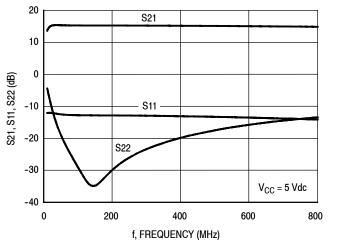


Figure 14. 50 Ohm Test Circuit Schematic



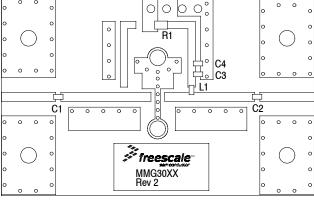


Figure 15. S21, S11 and S22 versus Frequency

Figure 16. 50 Ohm Test Circuit Component Layout

Table 8. 50 Ohm Test Circuit Component Designations and Values

Part	Part Description		Manufacturer
C1, C2	0.01 μF Chip Capacitors	C0603C103J5RAC	Kemet
C3	0.1 μF Chip Capacitor	C0603C104J5RAC	Kemet
C4	1 μF Chip Capacitor	C0603C105J5RAC	Kemet
L1	470 nH Chip Inductor	BK2125HM471-T	Taiyo Yuden
R1	0 Ω, 1/10 W Chip Resistor	CRCW06030000FKEA	Vishay

## 50 OHM APPLICATION CIRCUIT: 800-3600 MHz

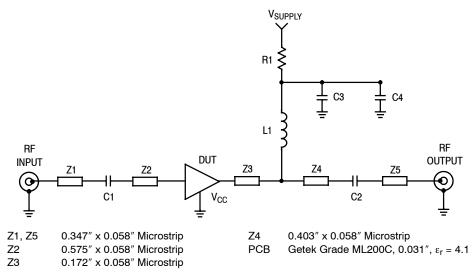


Figure 17. 50 Ohm Test Circuit Schematic

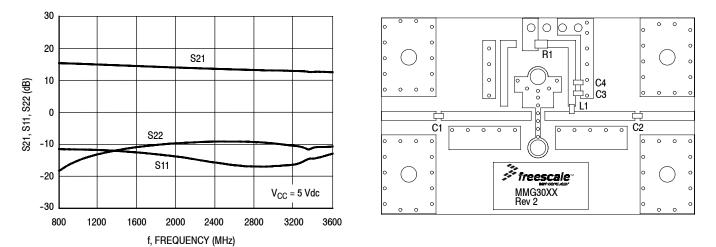


Figure 18. S21, S11 and S22 versus Frequency

Figure 19. 50 Ohm Test Circuit Component Layout

Table 9. 50 Ohm Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
C1, C2	150 pF Chip Capacitors	C0603C151J5RAC	Kemet
СЗ	0.1 μF Chip Capacitor	C0603C104J5RAC	Kemet
C4	1 μF Chip Capacitor	C0603C105J5RAC	Kemet
L1	56 nH Chip Inductor	HK160856NJ-T	Taiyo Yuden
R1	0 Ω, 1/10 W Chip Resistor	CRCW06030000FKEA	Vishay

Table 10. Common Emitter S-Parameters ( $V_{CC}$  = 5 Vdc,  $T_A$  = 25°C, 50 Ohm System)

f	5	S <sub>11</sub>	S	21	S	12	5	22
MHz	S <sub>11</sub>	∠ ¢	S <sub>21</sub>	∠ <b>φ</b>	S <sub>12</sub>	∠ ¢	S <sub>22</sub>	∠ <b>φ</b>
200	0.28	174.23	6.17	171.48	0.08	-2.66	0.06	-43.26
250	0.28	172.92	6.16	169.36	0.08	-3.32	0.07	-50.81
300	0.27	171.92	6.15	167.25	0.08	-3.93	0.08	-56.75
350	0.27	170.57	6.14	165.15	0.08	-4.60	0.09	-62.45
400	0.27	169.49	6.12	163.07	0.08	-5.22	0.09	-67.13
450	0.26	168.53	6.11	160.97	0.08	-5.85	0.10	-71.09
500	0.26	167.16	6.10	158.87	0.08	-6.50	0.11	-74.88
550	0.26	165.92	6.08	156.78	0.08	-7.14	0.12	-77.99
600	0.26	164.77	6.06	154.73	0.08	-7.76	0.13	-81.75
650	0.26	163.38	6.05	152.65	0.08	-8.41	0.14	-85.06
700	0.25	162.57	6.03	150.58	0.08	-9.03	0.14	-88.16
750	0.25	161.36	6.01	148.53	0.08	-9.64	0.15	-91.28
800	0.25	160.35	5.99	146.50	0.08	-10.26	0.16	-93.96
850	0.25	159.29	5.97	144.45	0.08	-10.88	0.17	-96.90
900	0.25	158.03	5.95	142.41	0.08	-11.52	0.18	-99.99
950	0.24	157.14	5.93	140.38	0.08	-12.14	0.18	-102.70
1000	0.24	156.02	5.91	138.38	0.08	-12.78	0.19	-105.47
1050	0.24	154.89	5.88	136.37	0.08	-13.38	0.20	-108.27
1150	0.24	153.09	5.83	132.34	0.08	-14.64	0.21	-114.23
1200	0.24	152.30	5.80	130.37	0.08	-15.28	0.22	-117.17
1250	0.24	151.41	5.77	128.39	80.0	-15.94	0.22	-120.26
1300	0.24	150.63	5.75	126.41	80.0	-16.57	0.23	-123.42
1350	0.24	150.09	5.72	124.46	0.08	-17.17	0.24	-126.34
1400	0.24	149.52	5.69	122.50	0.08	-17.81	0.24	-129.61
1450	0.24	149.15	5.67	120.54	80.0	-18.46	0.25	-132.32
1500	0.23	148.71	5.65	118.61	0.08	-19.07	0.26	-134.63
1550	0.23	147.76	5.62	116.65	0.08	-19.73	0.26	-136.77
1600	0.23	146.51	5.60	114.72	0.08	-20.39	0.27	-138.90
1650	0.23	145.11	5.57	112.79	0.08	-21.04	0.28	-141.13
1900	0.23	138.41	5.41	103.23	0.08	-24.38	0.31	-152.46
2150	0.24	132.77	5.23	93.77	0.08	-27.79	0.35	-163.83
2400	0.25	128.41	5.05	84.48	0.08	-31.33	0.38	-175.54
2650	0.26	124.16	4.87	75.21	0.08	-35.09	0.40	172.45
2900	0.28	119.27	4.69	66.04	0.08	-39.03	0.43	161.50
2950	0.28	118.39	4.65	64.24	0.08	-39.86	0.44	159.35
3000	0.28	117.49	4.62	62.43	0.09	-40.65	0.44	157.23
3050	0.28	116.75	4.59	60.59	0.09	-41.48	0.45	154.83
3100	0.29	116.03	4.55	58.77	0.09	-42.33	0.46	152.37
3150	0.29	115.21	4.52	56.97	0.09	-43.16	0.46	150.02
3200	0.29	114.41	4.48	55.15	0.09	-44.01	0.47	147.68
3250	0.29	113.69	4.44	53.36	0.09	-44.83	0.48	145.58
3300	0.29	112.97	4.41	51.59	0.09	-45.67	0.48	143.48
3350	0.29	112.24	4.37	49.84	0.09	-46.48	0.49	141.43

(continued)

Table 10. Common Emitter S-Parameters ( $V_{CC}$  = 5 Vdc,  $T_A$  = 25°C, 50 Ohm System) (continued)

f	S	11	S	21	S	12	S	22
MHz	S <sub>11</sub>	∠ ф	S <sub>21</sub>	∠ ф	S <sub>12</sub>	∠ ф	S <sub>22</sub>	∠ <b>φ</b>
3400	0.29	111.50	4.34	48.07	0.09	-47.31	0.49	139.46
3450	0.29	110.37	4.30	45.96	0.09	-48.32	0.50	137.08
3500	0.29	109.50	4.27	44.53	0.09	-49.01	0.50	135.57
3550	0.29	108.57	4.23	42.83	0.09	-49.82	0.51	133.81
3600	0.29	107.57	4.20	41.14	0.09	-50.64	0.52	132.08

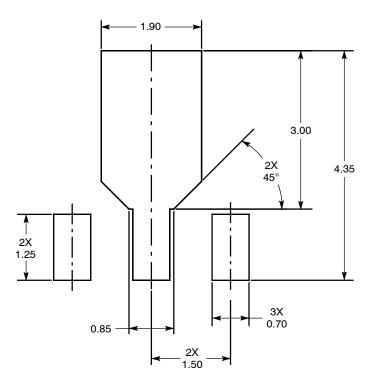
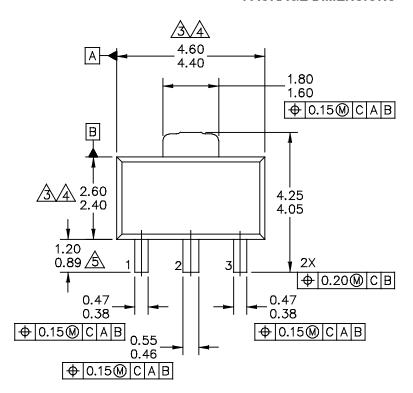


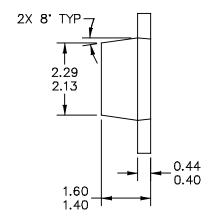
Figure 20. PCB Pad Layout for SOT-89A

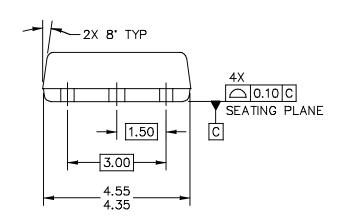


Figure 21. Product Marking

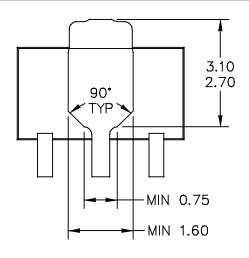
# **PACKAGE DIMENSIONS**







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TITLE:		DOCUMENT NO	): 98ASA00241D	REV: 0
SOT-89A, 3 LEAI	CASE NUMBER	R: 2142–01	15 JUL 2010	
4.5 X 2.5 PKG, 1.5 MW	I PIICH	STANDARD: NO	N-JEDEC	



BOTTOM VIEW

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SOT-89A, 3 LEAD,		DOCUMENT NO: 98ASA00241D		REV: 0
		CASE NUMBER: 2142-01		15 JUL 2010
4.5 X 2.5 PKG, 1.5 MM	I PIICH	STANDARD: NON-JEDEC		

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
- 2. ALL DIMENSIONS ARE IN MILLIMETERS.



DIMENSIONS DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.5 MM PER END. DIMENSION DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.5 MM PER SIDE.



DIMENSION ARE DETERMINED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY EXCLUSIVE OF MOLD FLASH, TIE BAR BURRS, GATE BURRS AND INTERLEAD FLASH, BUT INCLUDING ANY MISMATCH BETWEEN THE TOP AND BOTTOM OF THE PLASTIC BODY.

<u>/5.</u>

TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

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TITLE: SOT-89A, 3 LEAD, 4.5 X 2.5 PKG, 1.5 MM PITCH		DOCUMENT NO	): 98ASA00241D	REV: 0
		CASE NUMBER: 2142-01		15 JUL 2010
		STANDARD: NON-JEDEC		

MMG3015NT1

# PRODUCT DOCUMENTATION, SOFTWARE AND TOOLS

Refer to the following documents, software and tools to aid your design process.

## **Application Notes**

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers
- AN3100: General Purpose Amplifier and MMIC Biasing

#### Software

• .s2p File

## **Development Tools**

· Printed Circuit Boards

For Software and Tools, do a Part Number search at http://www.freescale.com, and select the "Part Number" link. Go to the Software & Tools tab on the part's Product Summary page to download the respective tool.

## **REVISION HISTORY**

The following table summarizes revisions to this document.

Revision	Date	Description		
0	Aug. 2007	Initial Release of Data Sheet		
1	Apr. 2008	<ul> <li>Removed Footnote 2, Continuous voltage and current applied to device, from Table 2, Maximum Ratings, p. 1</li> <li>Corrected Fig. 13, Single-Carrier W-CDMA Adjacent Channel Power Ratio versus Output Power y-axis (ACPR) unit of measure to dBc, p. 5</li> <li>Updated Part Numbers in Tables 8, 9, Component Designations and Values, to latest RoHS compliant</li> </ul>		
		part numbers, p. 6, 7		
2	Feb. 2012	Corrected temperature at which ThetaJC is measured from 25°C to 95°C and added "no RF applied" to Thermal Characteristics table to indicate that thermal characterization is performed under DC test with no RF signal applied, p. 1		
		<ul> <li>Table 6, ESD Protection Characterization, removed the word "Minimum" after the ESD class rating. ESD ratings are characterized during new product development but are not 100% tested during production. ESD ratings provided in the data sheet are intended to be used as a guideline when handling ESD sensitive devices, p. 3</li> </ul>		
		<ul> <li>Removed I<sub>CC</sub> bias callout from applicable graphs and Table 10, Common Emitter S-Parameters heading as bias is not a controlled value, p. 4-9</li> </ul>		
		Added .s2p File availability to Product Software and Printed Circuit Boards to Development Tools, p. 14		
3	Sept. 2012	<ul> <li>Replaced the PCB Pad Layout drawing, the package isometric and mechanical outline for Case 1514-02 (SOT-89) with Case 2142-01 (SOT-89) as a result of the device transfer from a Freescale wafer fab to an external GaAs wafer fab and new assembly site. The new assembly and test site's SOT-89 package has slight dimensional differences., p. 1, 10-13. Refer to PCN13337, GaAs Fab Transfer.</li> <li>Added Fig. 21, Product Marking, p. 10</li> </ul>		

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